

OBUDA UNIVERSITY



Doctoral School on Materials Sciences and Technologies

Institute of Technical Physics and Materials Science
Centre for Energy Research

5th Semester Report On ' Non-Destructive Optical Mapping Tool From Cheap Parts '

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1. Introduction

Spectroscopic Ellipsometry (SE)

- Non-destructive, non-invasive and non-intrusive optical technique.
- Measures the relative change in polarization state of the measurement beam.
- The two SE measurable values: Amplitude ratio (Ψ) and phase difference (Δ) between the **p**- and **s**-polarizations.
- Ψ and Δ are related to the wavelength of the light beam ' λ ' and the angle of incidence of the beam ' θ ' at the sample surface, respectively.
- Major Steps: Measurement, Data interpretation, Modelling, Fitting, Evaluation and Results.

1.1. Aim of the Research

- Making an optical mapping tool *prototype* from cheap parts like:
Tablets, monitors and big screen LCD,LED TV
- Programming the data collection and data processing software
- Making measurements on selected samples and determining the precision of the prototype.

1.2. Research Methods

Original Concept of Prototype building using different parts

1. Light-source
(LED-panel)
2. Diffuser sheet
3. Film-polarizer
4. Analyzer

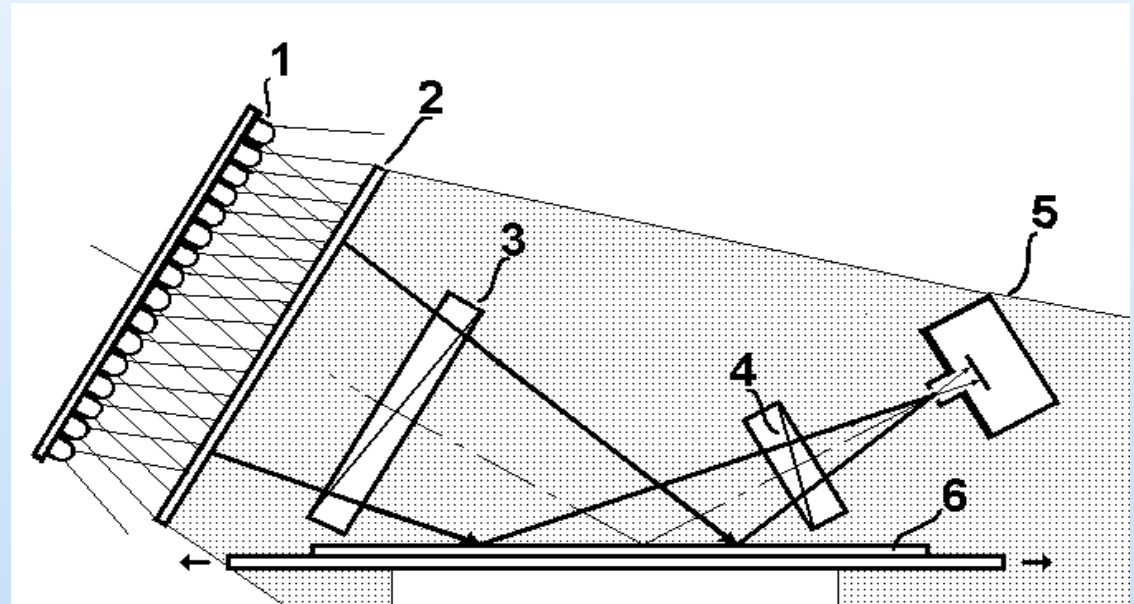


Fig. 1: Original concept of the non-collimated beam ellipsometer

5. Detector
(pin-hole + CCD-detector) and
6. Sample

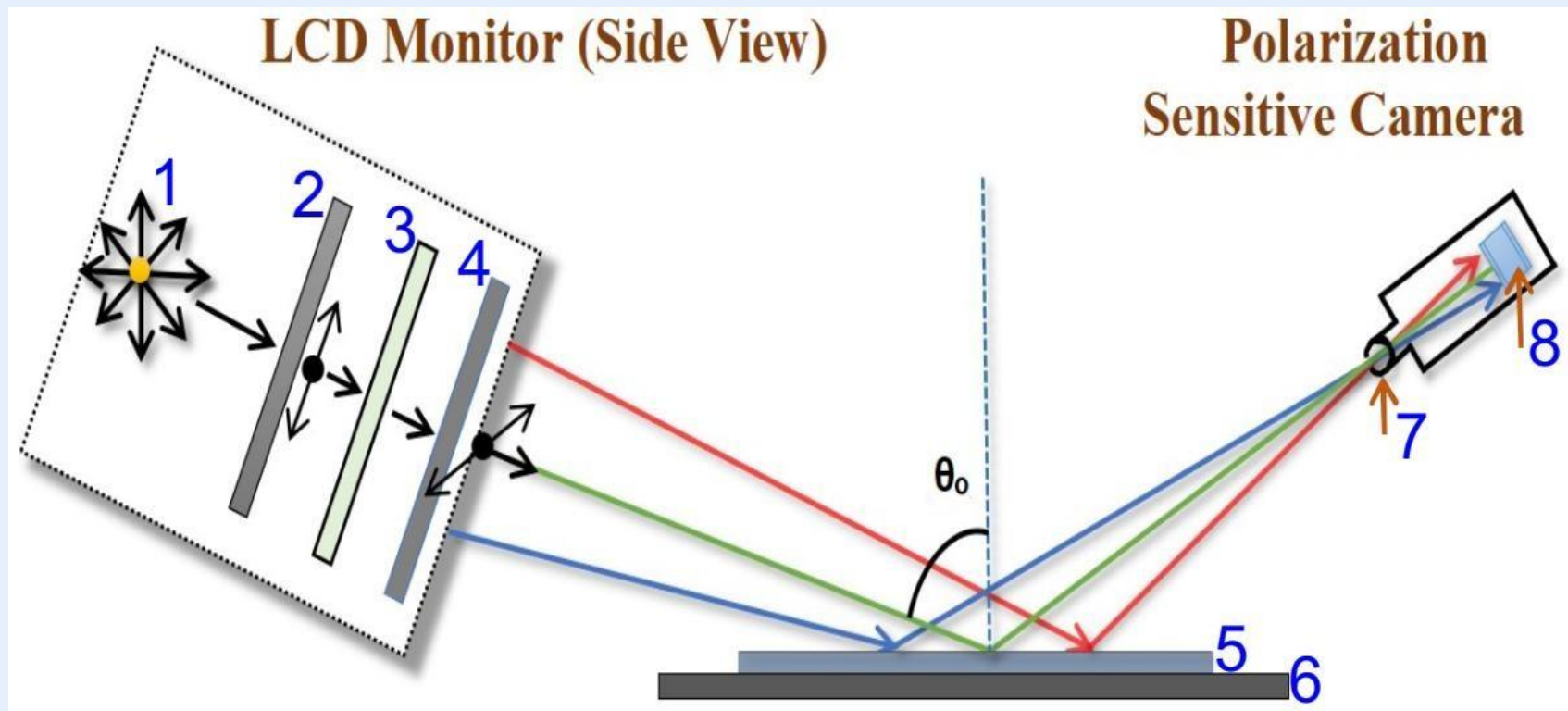
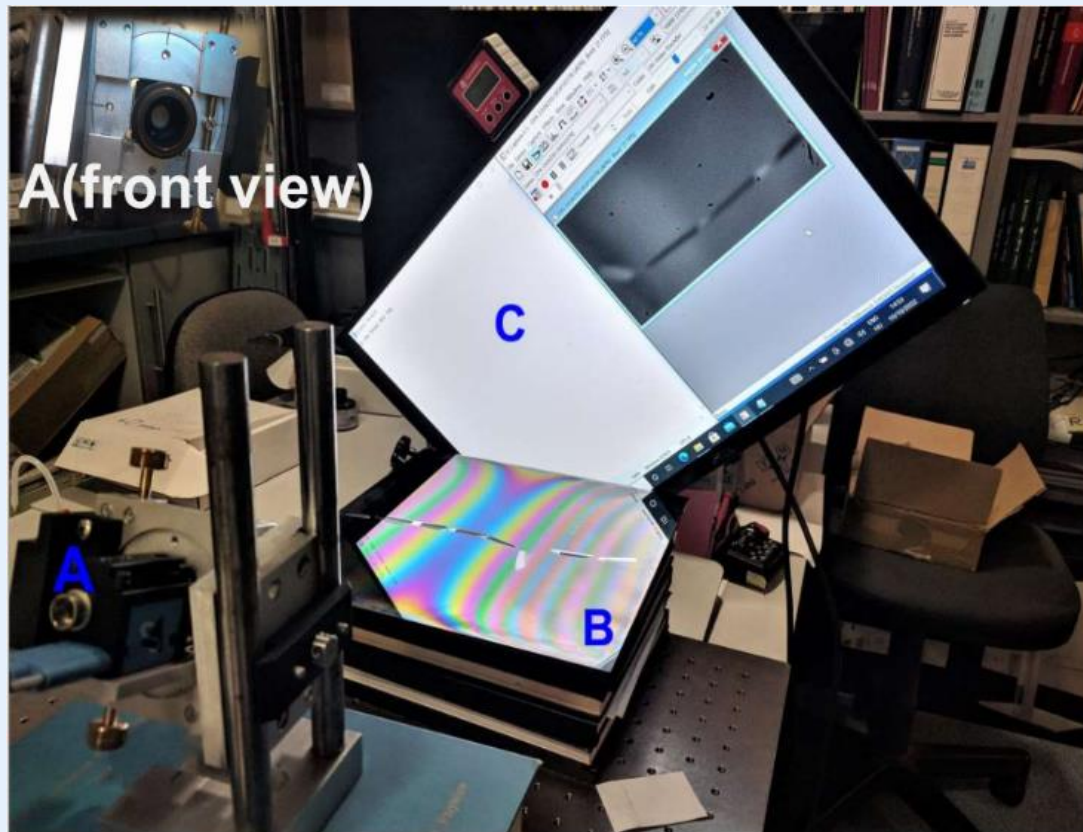


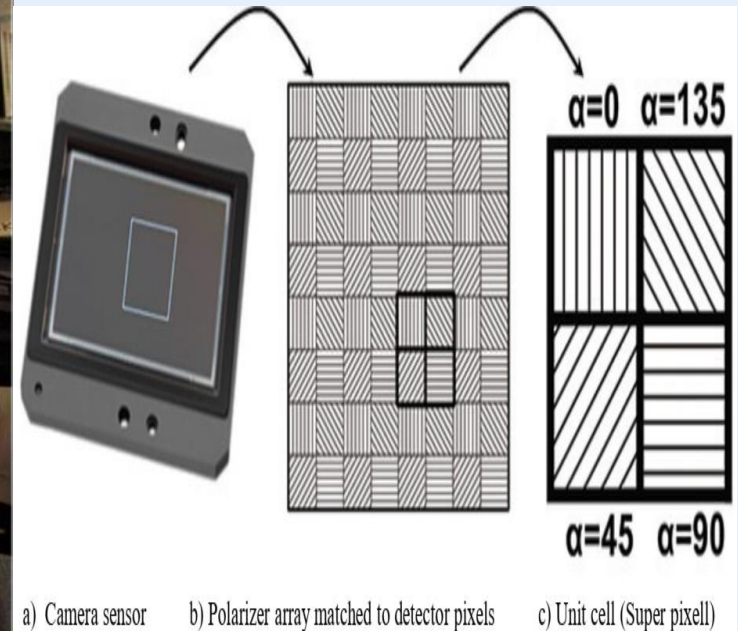
Fig. 2: New concept of the non-collimated beam ellipsometer prototype from cheap parts

- | | | |
|-------------------------------|-----------------------|------------------------|
| 1) Light source | 2) Vertical polarizer | 3) Liquid crystal cell |
| 4) Horizontal polarizer | 5) Sample | 6) Sample holder |
| 7) Pin hole (sub-mm size) and | 8) Camera sensor | |

The new concept is without the rotating polarizers



a)



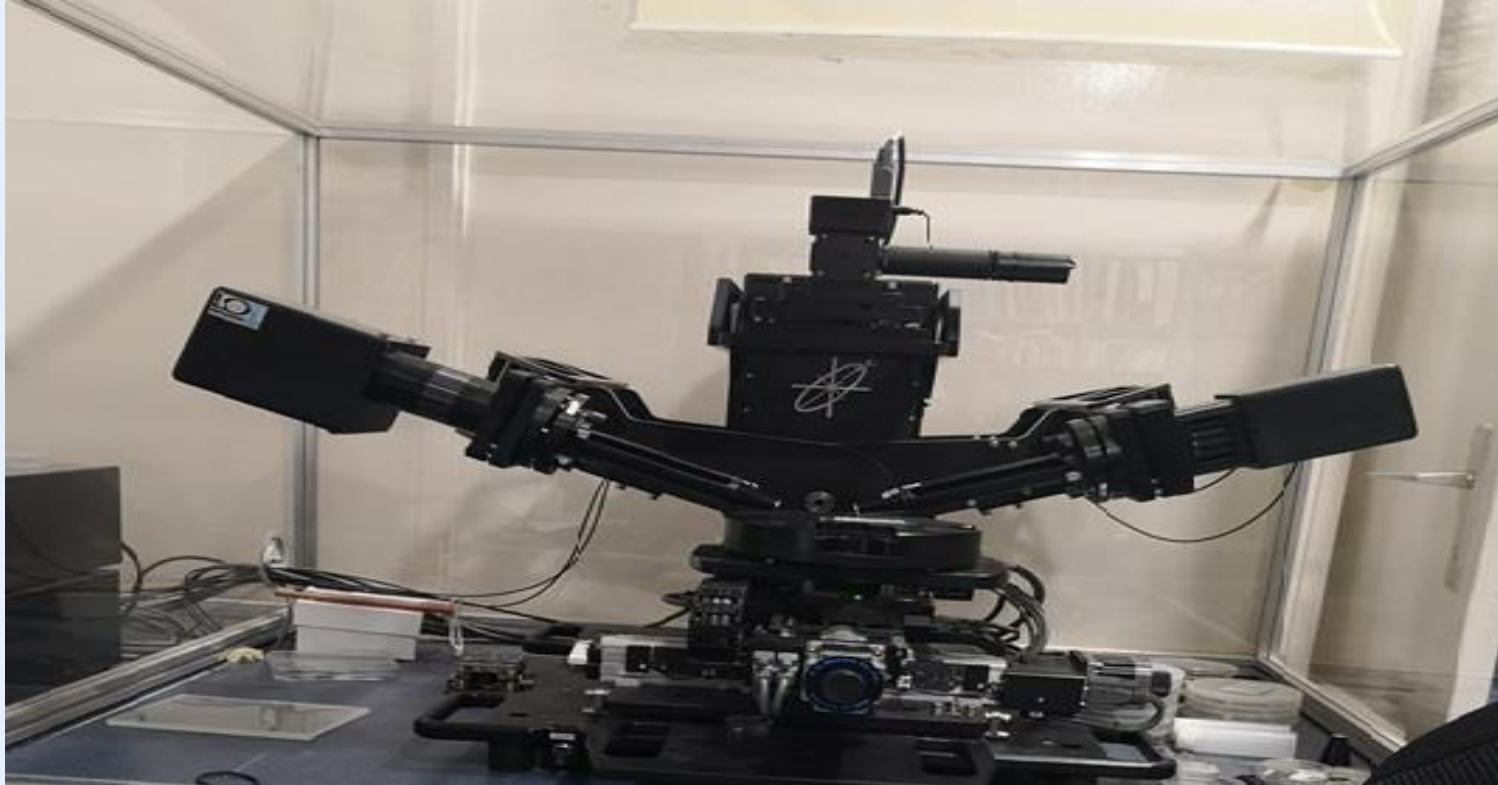
b)

Fig. 3: a) Experimental set up

A) Polarization sensitive camera B) Sample + holder C) LCD monitor

b) Schematic structure (CMOS Pregius Polarsens sensor),
NB. CMOS sensor is Integrated 4-Directional Wire Grid Polarizer

1.3. Characterization methods



- **Fig. 4:** Rotating Compensator Spectroscopic Ellipsometer (M2000DI)
- The M2000DI ellipsometer is used for control measurements.

Rotating Compensator Spectroscopic Ellipsometer

- Provides fast and very accurate thin film characterization over a wide spectroscopic range.
- Measures film thickness and optical constants on single or multilayer stack.
- Extreme sensitivity for very thin over layers even below 1 nm thickness.
- But it is indirect analysis technique.
- Similar measurements will help the calibration of the prototype.

2. Results of the Previous Semester

- 60nm, SiO_2/Si sample *angle of incidence*(AOI) calibration, thickness measurement, MSE analysis was done.
- Only, less than 2 nm thickness difference between the M2000 and our prototype, with very low MSE.

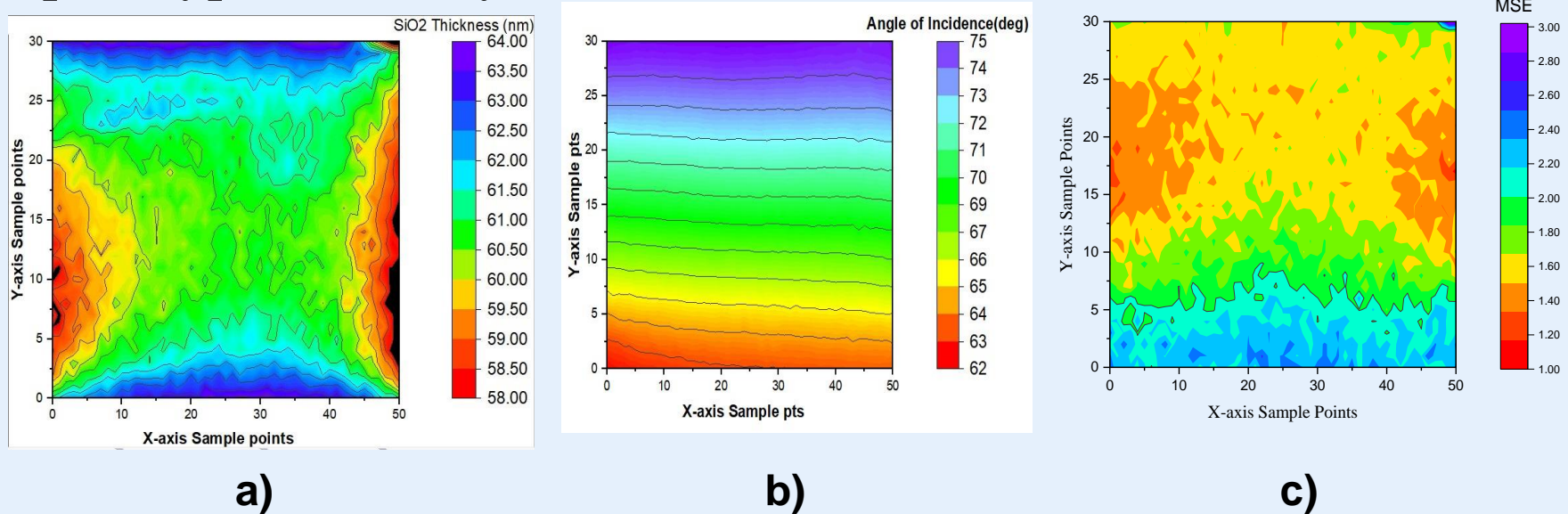
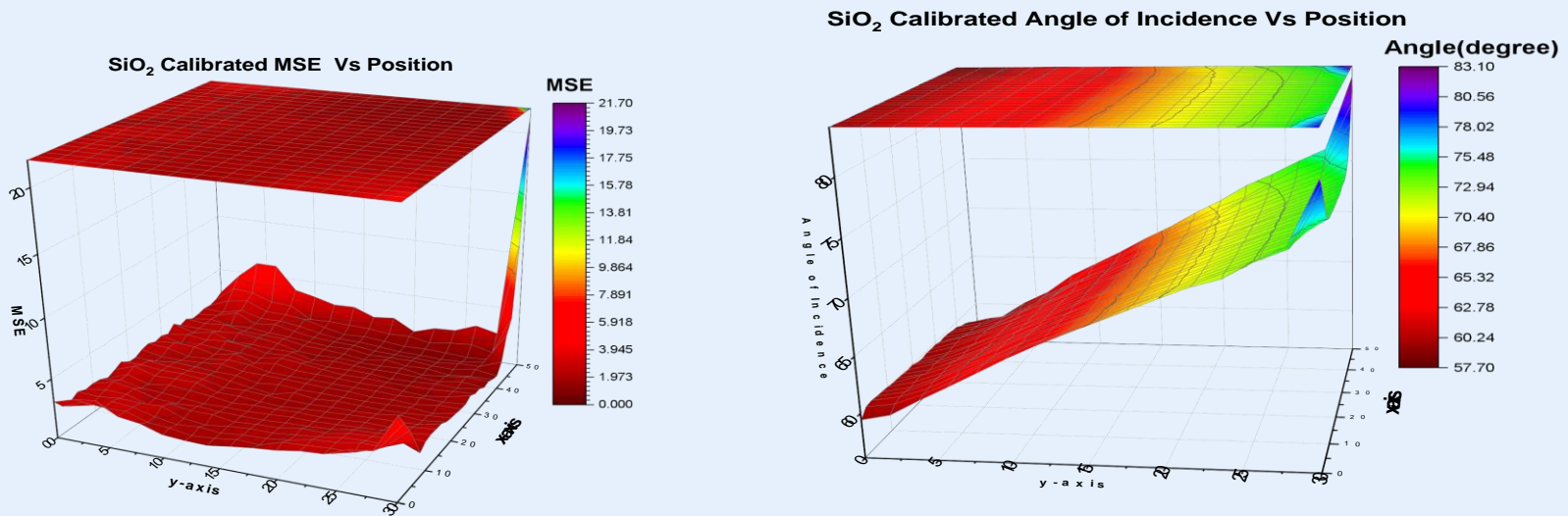


Fig. 5: a) Thickness vs position
b) Angle of incidence versus position
c) MSE vs position

2. Results of the Previous Semester

- A SiO_2/Si samples on three different positions, hence a better calibration was done.
- A *Poly-Si-on-SiO₂* samples, a $\text{WO}_3\text{-MoO}_3$ combinatorial mixed layers on a 30x30 cm glass sheet,
- A chessboard-like etched silicon dioxide-covered silicon wafer and other experiments were done and reported.



- **Fig 6.** 3D ,MSE and angle of incidence calibration vs position.

3. Results of the Actual Semester

Actual Semester Aim :

- Calibration of the Prototype.
- A measurement on SiO_2 on Si substrate was done on three different sample thicknesses, 60nm, 80nm and 100nm each at more than three different positions, automated with Matlab code software
- Below are some Matlab automated measurement images for a SiO_2/Si samples of 60nm, 80nm and 100nm as a startup respectively.

3. Results of the Actual Semester

3.1 60nm SiO₂

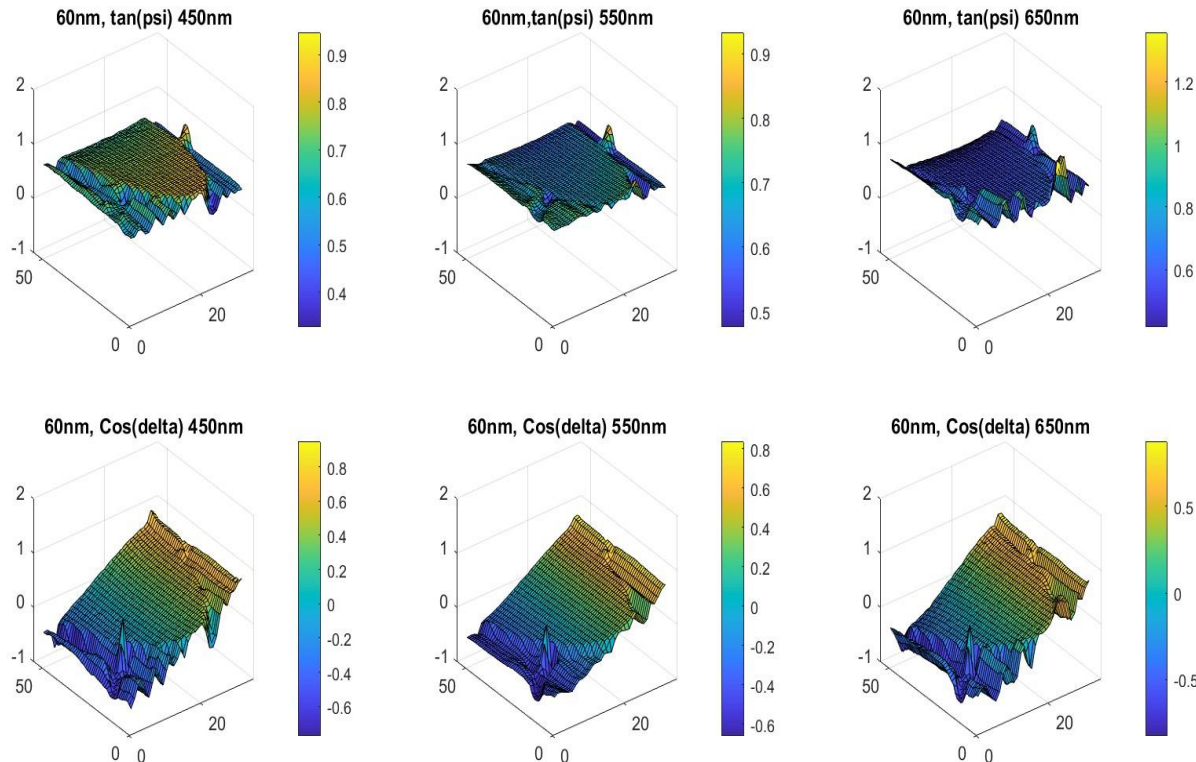


Fig. 7: A 60nm SiO₂/Si sample $\tan(\Psi)$ and $\cos(\Delta)$ measurements for RGB spectrum

3. Results of the Actual Semester

3.1 80nm SiO₂

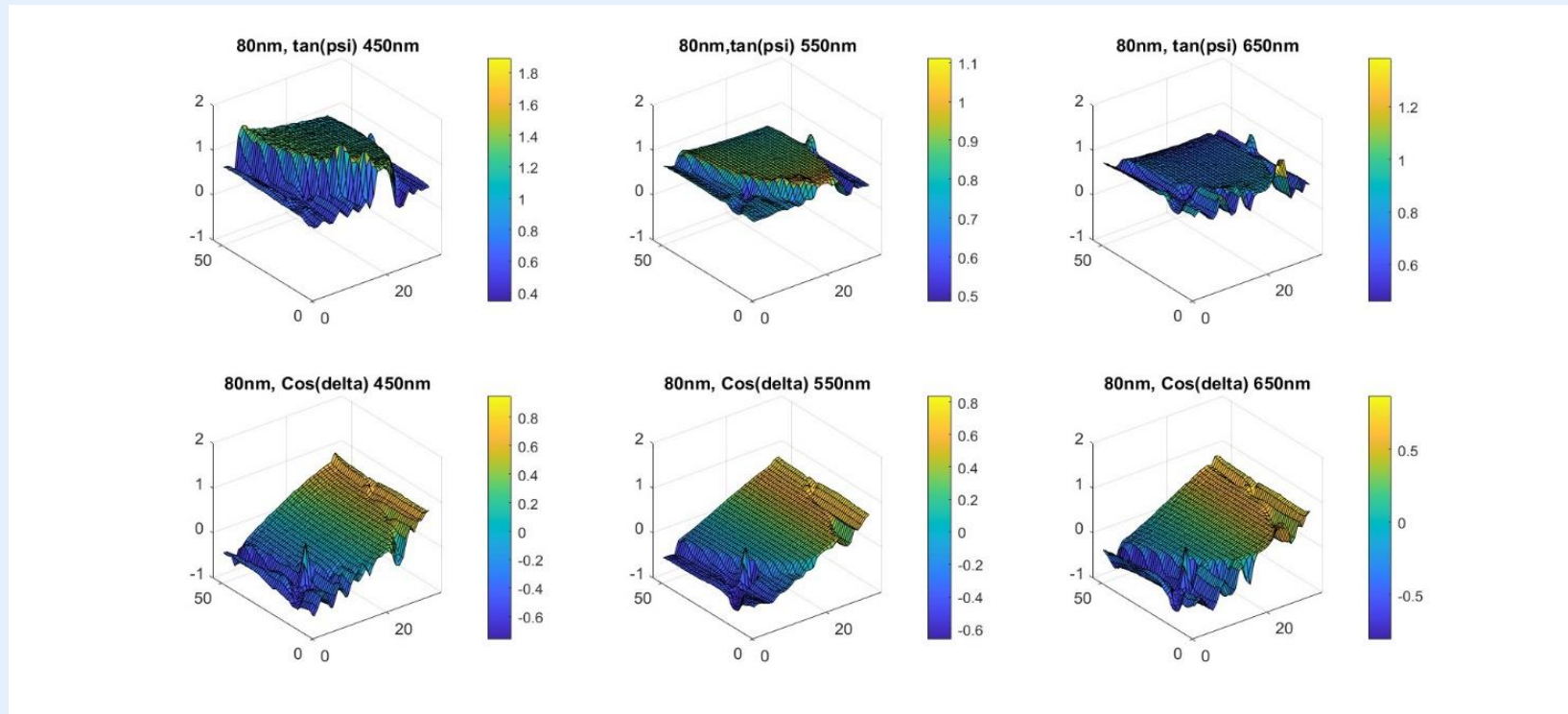


Fig. 8: A 80nm SiO₂/Si sample $\tan(\Psi)$ and $\cos(\Delta)$ measurements for RGB spectrum.

3. Results of the Actual Semester

3.1 100 nm SiO₂ calibration

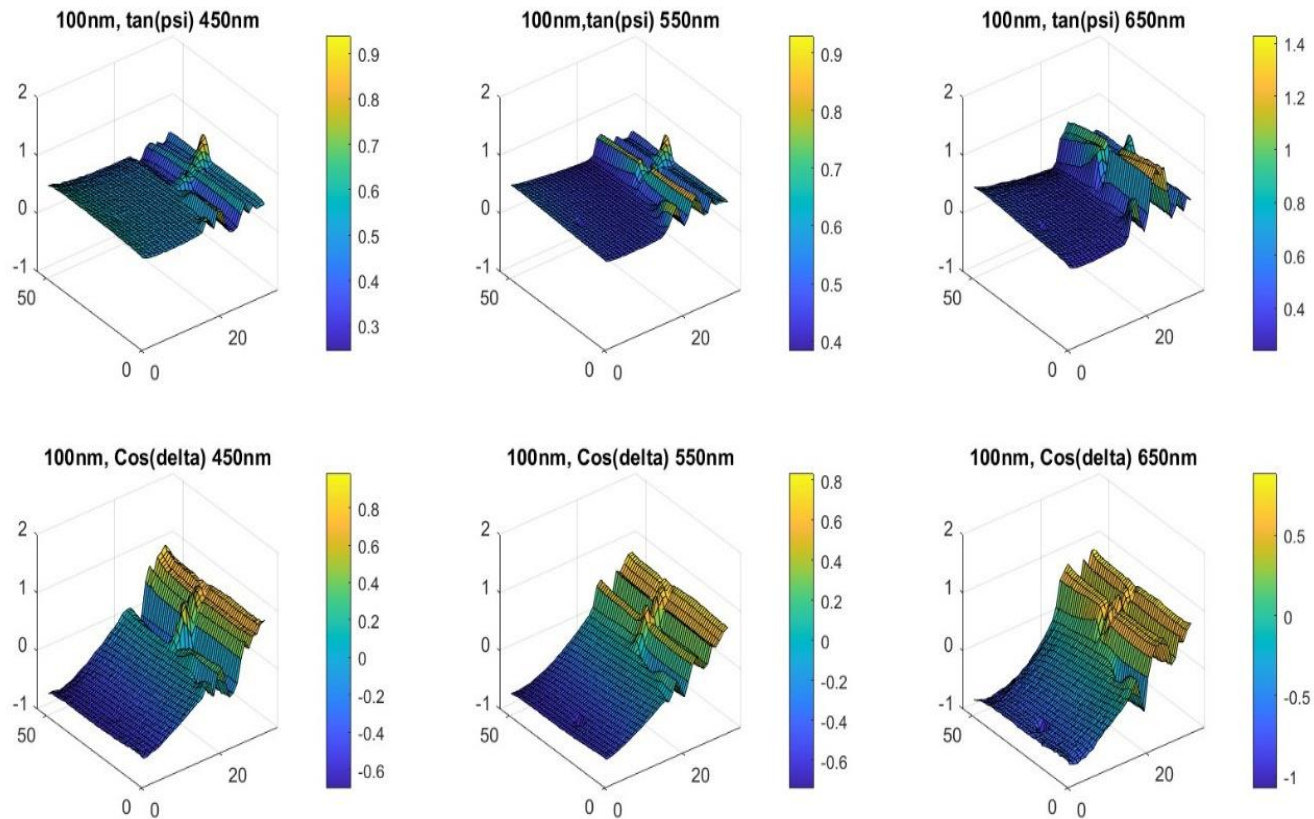


Fig. 9: A 100nm SiO₂/Si sample $\tan(\Psi)$ and $\cos(\Delta)$ measurements for RGB spectrum

General View of the Prototype tool

Advantages

- The new prototype is fast imaging and made up of cheap parts
- Wide mapping area up to 150cm is possible .

Limitations

- Only three wide wavelength bands (RGB) are in action ,which narrows the range of the light band source.
- '0.1 degree' angle uncertainty from the digital angle gauge used in rotation angle of the LCD, which affects incident polarization state of the light.

Current Semester Activities

- 12th Workshop on Spectroscopic Ellipsometry (WSE) , September 19-21, 2023 in Prague, in the Czech Republic.
- Budapest School **on Modern X-ray Science 2023** (October 3-6 , 2023)
- Surface Science Discussions 2024 – Programme , January 9-10, 2024, Online
- and many other online seminars.

4. Plans For the Future Work

- Full calibration of the prototype with automated data analysis and get the apparatus ready for new different samples, Silicon derived thin films and different samples as required.

köszönöm !